

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	29	("Hf.sub N" hafnium near3 nitride) near10 gate near3 electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 17:36
L2	55	(hafnium adj nitride or Hf\$1N\$2) near6 gate and (CMOS complementary near3 metal near3 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 17:59
L3	3	("20040256679" "20050101134" "6642097").PN. OR ("7098516").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/30 17:57
L4	2	("20040012043").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/30 17:57
L5	322	(hafnium adj nitride "Hf.sub. N" Hf\$1N\$2) and (CMOS complementary near3 metal near3 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 20:22
L6	19	CMOS and (hafnium near3 oxide "HfO.sub.2") near7 (MOCVD)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 20:40
L8	43	CMOS and (hafnium near3 oxide "HfO.sub.2") near7 (nitrogen "N. sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 20:41
L9	5	CMOS and (hafnium near3 oxide "HfO.sub.2") near7 (nitrogen "N. sub.2") near3 anneal\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 20:53

EAST Search History

L10	23	atomic near5 ("N.sub.2" nitrogen) near3 (hafnium Hf)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 20:56
L11	10	(hafnium near3 nitride hfN) near7 (dop\$3 impurit\$3 implant\$ ion) and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:03
L12	199	(hafnium near3 nitride hfN) near7 (nitride "N.sub.2") and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:05
L13	24	(hafnium near3 nitride hfN) near7 (nitrogen "N.sub.2") and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:22
L14	10	(hafnium adj nitride hfN) near7 (nitrogen "N.sub.2") and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:23
L15	448	(hafnium "hf") near7 (nitrogen "N. sub.2") and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:42
L16	265	(hafnium near3 nitride "HfN") and (RTA rapid near2 thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:43
L17	1	(hafnium near3 nitride "HfN") near7 (RTA rapid near2 thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:43

EAST Search History

L18	2	(hafnium near3 nitride "HfN") near10 (RTA rapid near2 thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:43
L19	2	(hafnium near3 nitride "HfN") with (RTA rapid near2 thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:52
L20	109	("TaN" tantalum adj nitride) and ("HfN" hafnium adj nitride) and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 21:53
S3	8	(metal adj gate) and (hafnium adj nitride) and Hfn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 10:32
S46	0	(hafnium near2 nitride) near5 (cap\$3) near5 dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/02 14:44
S47	78	(hafnium near3 nitride) and cap\$3 and dielectric	US-PGPUB	OR	ON	2006/09/02 14:48
S48	42	(hafnium near3 nitride) and cap\$3 and dielectric and source and drain	US-PGPUB	OR	ON	2006/09/02 14:52
S49	2	("20050205947").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/02 14:52
S50	495	(hafnium near3 nitride HfN) and (Cap\$3 TaN Tantalum near3 nitiride) and (dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/02 14:59

EAST Search History

S51	390	S50 and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/02 14:55
S52	199	((hafnium near3 nitride HfN) near10 (Cap\$3 TaN Tantalum near3 nitride)) and (dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/02 15:01
S53	199	((hafnium near3 nitride HfN) near10 (Cap\$3 TaN Tantalum near3 nitride)) and (dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/02 15:01
S54	438	(hafnium near3 nitride or Hf\$1N\$2) and (dielectric insulat\$3) and (CMOS complementary near3 metal near3 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:49
S55	22	((("6225168") or ("6383879") or ("6511911") or ("6617624") or ("6043157") or ("5960270") or ("6083836") or ("6576967") or ("6479362") or ("6208004") or ("6051487"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 10:36
S56	2	S55 and (hafnium near2 nitride hf\$2n\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:37
S57	316	(hafnium adj nitride or Hf\$1N\$2) and (CMOS complementary near3 metal near3 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/30 17:43